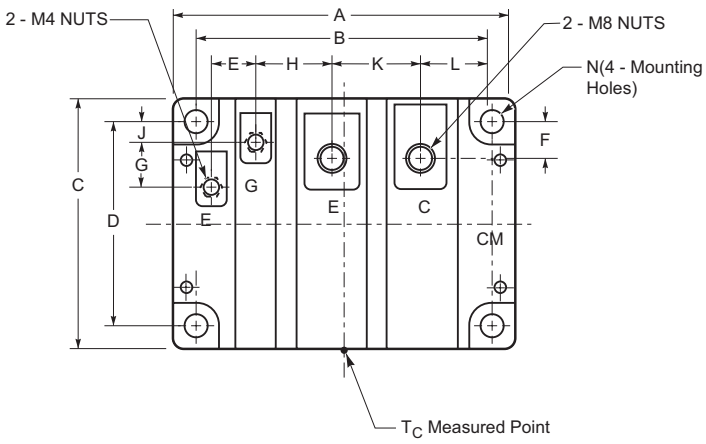
MITSUBISHI IGBT MODULES

# CM600HU-24H

**HIGH POWER SWITCHING USE**
**INSULATED TYPE**




**Outline Drawing and Circuit Diagram**

**Description:**
Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of one IGBT in a single configuration with a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

**Features:**
- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy Heat Sinking

**Applications:**
- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

**Ordering Information:**
Example: Select the complete module number you desire from the table - i.e. CM600HU-24H is a 1200V ($V_{CES}$), 600 Ampere Single IGBT Module.

| Type | Current Rating Amperes | $V_{CES}$ Volts (x 50) |
|---|---|---|
| CM | 600 | 24 |

| Dimensions | Inches | Millimeters |
|---|---|---|
| A | 4.33 | 110.0 |
| B | 3.66±0.01 | 93.0±0.25 |
| C | 3.15 | 80.0 |
| D | 2.44±0.01 | 62.0±0.25 |
| E | 0.53 | 13.5 |
| F | 0.37 | 9.5 |
| G | 0.57 | 14.5 |

| Dimensions | Inches | Millimeters |
|---|---|---|
| H | 0.96 | 24.5 |
| J | 0.22 | 5.5 |
| K | 1.14 | 29.0 |
| L | 0.85 | 21.5 |
| M | 1.34 +0.04/-0.02 | 34 +1.0/-0.5 |
| N | 0.26 Dia. | 6.5 Dia. |
| P | 1.02 +0.04/-0.02 | 26 +1.0/-0.5 |



MITSUBISHI ELECTRIC

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### Absolute Maximum Ratings, $T_j$ = 25 °C unless otherwise specified

| Ratings | Symbol | CM600HU-24H | Units |
|---|---|---|---|
| Junction Temperature | $T_j$ | -40 to 150 | °C |
| Storage Temperature | $T_{stg}$ | -40 to 125 | °C |
| Collector-Emitter Voltage (G-E SHORT) | $V_{CES}$ | 1200 | Volts |
| Gate-Emitter Voltage (C-E SHORT) | $V_{GES}$ | ±20 | Volts |
| Collector Current ($T_c$ = 25°C) | $I_C$ | 600 | Amperes |
| Peak Collector Current ($T_j \leq$ 150°C) | $I_{CM}$ | 1200* | Amperes |
| Emitter Current** ($T_c$ = 25°C) | $I_E$ | 600 | Amperes |
| Peak Emitter Current** | $I_{EM}$ | 1200* | Amperes |
| Maximum Collector Dissipation ($T_c$ = 25°C) | $P_c$ | 3100 | Watts |
| Mounting Torque, M8 Main Terminal | – | 8.8~10.8 | N · m |
| Mounting Torque, M6 Mounting | – | 3.5~4.5 | N · m |
| Mounting Torque, M4 Terminal | – | 1.3~1.7 | N · m |
| Weight | – | 600 | Grams |
| Isolation Voltage (Main Terminal to Baseplate, AC 1 min.) | $V_{iso}$ | 2500 | Vrms |

* Pulse width and repetition rate should be such that the device junction temperature ($T_j$) does not exceed $T_{j(max)}$ rating.
**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDi).

### Static Electrical Characteristics, $T_j$ = 25 °C unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| Collector-Cutoff Current | $I_{CES}$ | $V_{CE} = V_{CES}$, $V_{GE}$ = 0V | – | – | 2 | mA |
| Gate Leakage Voltage | $I_{GES}$ | $V_{GE} = V_{GES}$, $V_{CE}$ = 0V | – | – | 0.5 | µA |
| Gate-Emitter Threshold Voltage | $V_{GE(th)}$ | $I_C$ = 60mA, $V_{CE}$ = 10V | 4.5 | 6 | 7.5 | Volts |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C$ = 600A, $V_{GE}$ = 15V, $T_j$ = 25°C | – | 2.9 | 3.7 | Volts |
| | | $I_C$ = 600A, $V_{GE}$ = 15V, $T_j$ = 125°C | – | 2.85 | – | Volts |
| Total Gate Charge | $Q_G$ | $V_{CC}$ = 600V, $I_C$ = 600A, $V_{GE}$ = 15V | – | 2250 | – | nC |
| Emitter-Collector Voltage* | $V_{EC}$ | $I_E$ = 600A, $V_{GE}$ = 0V | – | – | 3.2 | Volts |

* Pulse width and repetition rate should be such that the device junction temperature ($T_j$) does not exceed $T_{j(max)}$ rating.

### Dynamic Electrical Characteristics, $T_j$ = 25 °C unless otherwise specified

| Characteristics | | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|---|
| Input Capacitance | | $C_{ies}$ | $V_{CE}$ = 10V, $V_{GE}$ = 0V | – | – | 90 | nF |
| Output Capacitance | | $C_{oes}$ | | – | – | 31.5 | nF |
| Reverse Transfer Capacitance | | $C_{res}$ | | – | – | 18 | nF |
| Resistive | Turn-on Delay Time | $t_{d(on)}$ | $V_{CC}$ = 600V, $I_C$ = 600A, | – | – | 300 | ns |
| Load | Rise Time | $t_r$ | $V_{GE1} = V_{GE2}$ = 15V, | – | – | 700 | ns |
| Switch | Turn-off Delay Time | $t_{d(off)}$ | $R_G$ = 2.1Ω, Resistive | – | – | 450 | ns |
| Times | Fall Time | $t_f$ | Load Switching Operation | – | – | 350 | ns |
| Diode Reverse Recovery Time | | $t_{rr}$ | $I_E$ = 600A, $di_E/dt$ = -1200A/µs | – | – | 300 | ns |
| Diode Reverse Recovery Charge | | $Q_{rr}$ | $I_E$ = 600A, $di_E/dt$ = -1200A/µs | – | 3.3 | – | µC |

### Thermal and Mechanical Characteristics, $T_j$ = 25 °C unless otherwise specified

| Characteristics | Symbol | Test Conditions | Min. | Typ. | Max. | Units |
|---|---|---|---|---|---|---|
| Thermal Resistance, Junction to Case | $R_{th(j-c)}Q$ | Per IGBT Module | – | – | 0.04 | °C/W |
| Thermal Resistance, Junction to Case | $R_{th(j-c)}D$ | Per FWDi Module | – | – | 0.06 | °C/W |
| Contact Thermal Resistance | $R_{th(c-f)}$ | Per Module, Thermal Grease Applied | – | 0.015 | – | °C/W |

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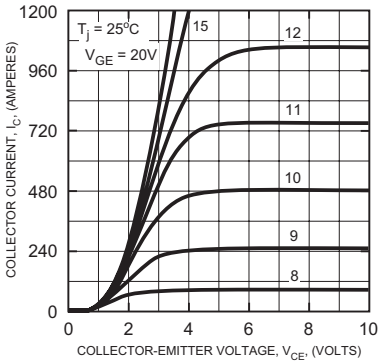
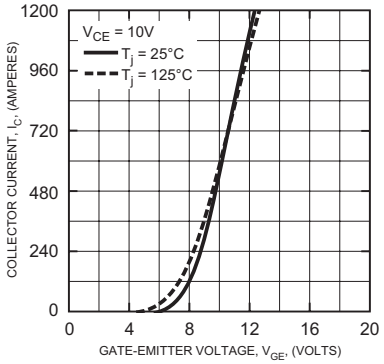
## HIGH POWER SWITCHING USE
## INSULATED TYPE

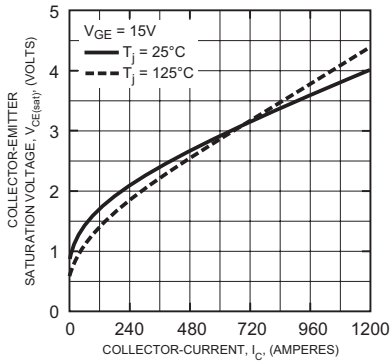
**OUTPUT CHARACTERISTICS (TYPICAL)**



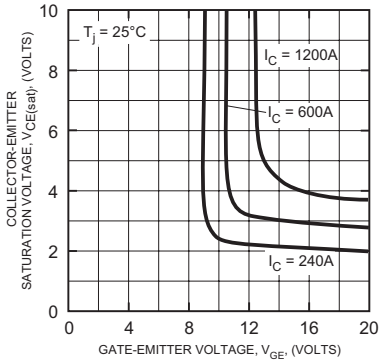

**TRANSFER CHARACTERISTICS (TYPICAL)**



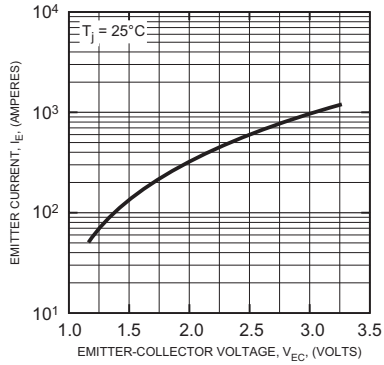

**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



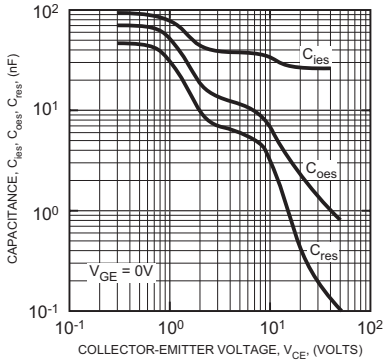

**COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)**



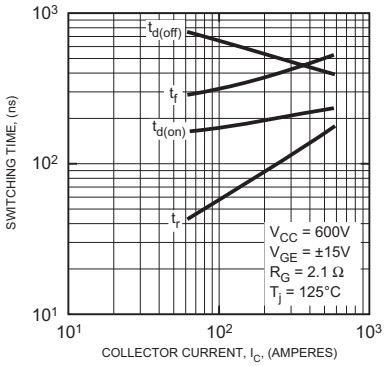

**FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**



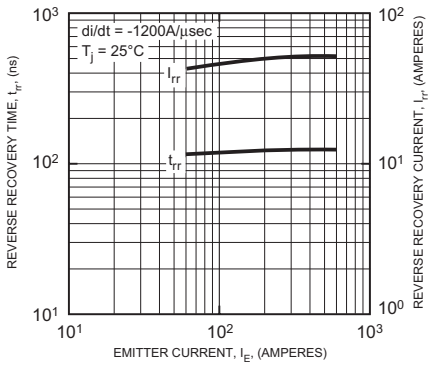

**CAPACITANCE VS. $V_{CE}$ (TYPICAL)**



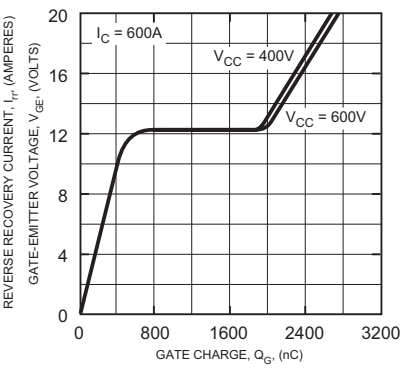

**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**




**REVERSE RECOVERY CHARACTERISTICS (TYPICAL)**




**GATE CHARGE, $V_{GE}$**



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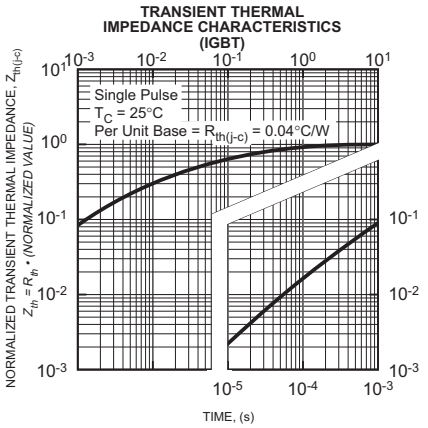
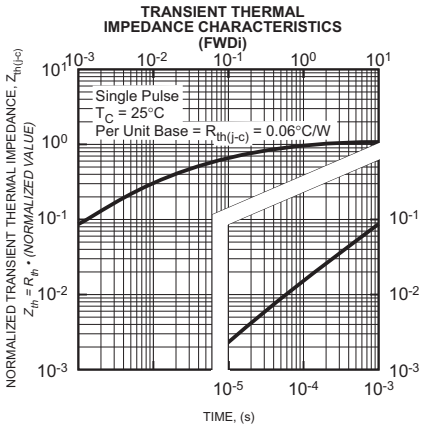

TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT)
NORMALIZED TRANSIENT THERMAL IMPEDANCE, $Z_{th(j-c)}$
$Z_{th} = R_{th} \cdot$ (NORMALIZED VALUE)
Single Pulse
$T_C$ = 25°C
Per Unit Base = $R_{th(j-c)}$ = 0.04°C/W
$10^{1}$
$10^{0}$
$10^{-1}$
$10^{-2}$
$10^{-3}$
$10^{-3}$ $10^{-2}$ $10^{-1}$ $10^{0}$ $10^{1}$
$10^{-5}$ $10^{-4}$ $10^{-3}$
TIME, (s)


TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(FWDi)
NORMALIZED TRANSIENT THERMAL IMPEDANCE, $Z_{th(j-c)}$
$Z_{th} = R_{th} \cdot$ (NORMALIZED VALUE)
Single Pulse
$T_C$ = 25°C
Per Unit Base = $R_{th(j-c)}$ = 0.06°C/W
$10^{1}$
$10^{0}$
$10^{-1}$
$10^{-2}$
$10^{-3}$
$10^{-3}$ $10^{-2}$ $10^{-1}$ $10^{0}$ $10^{1}$
$10^{-5}$ $10^{-4}$ $10^{-3}$
TIME, (s)